NEC

MOS FIELD EFFECT TRANSISTOR
2SK3573

SWITCHING
N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3573 is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, designed for low voltage high current applications such as DC/DC converter with synchronous rectifier.

★ ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3573	TO-220AB
2SK3573-S	TO-262
2SK3573-ZK	TO-263
2SK3573-Z	TO-220SMD Note

Note TO-220SMD package is produced only in Japan.

FEATURES

- 4.5 V drive available
- Low on-state resistance

  $R_{DS(on)1}$ = 4.0 mΩ MAX. (V_{GS} = 10 V, I_D = 42 A)
- Low gate charge

  Q_G = 68 nC TYP. (V_{DD} = 16 V, V_{GS} = 10 V, I_D = 83 A)
- Surface mount device available

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V_{GS} = 0 V)	V_{DSS}	20	V
Gate to Source Voltage (V_{DS} = 0 V)	V_{GSS}	±20	V
Drain Current (DC) (T_C = 25°C)	$I_{D(DC)}$	±83	A
Drain Current (pulse) Note	$I_{D(pulse)}$	±332	A
Total Power Dissipation (T_A = 25°C)	P_{T1}	1.5	W
Total Power Dissipation (T_C = 25°C)	P_{T2}	105	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	–55 to +150	°C

Note PW ≤ 10 μs, Duty Cycle ≤ 1%

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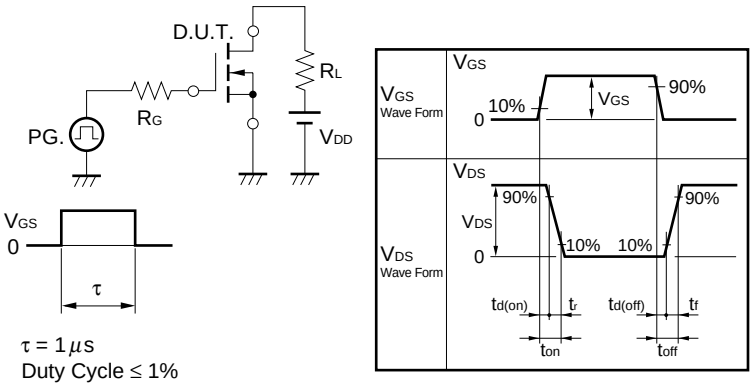
The mark ★ shows major revised points.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

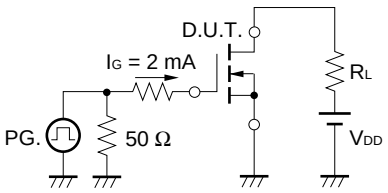
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V			10	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
Gate Cut-off Voltage	$V_{GS(off)}$	V_{DS} = 10 V, I_D = 1 mA	1.5		2.5	V
Forward Transfer Admittance	$\|y_{fs}\|$	V_{DS} = 10 V, I_D = 42 A	27			S
Drain to Source On-state Resistance	$R_{DS(on)1}$	V_{GS} = 10 V, I_D = 42 A		2.9	4.0	mΩ
	$R_{DS(on)2}$	V_{GS} = 4.5 V, I_D = 42 A		3.8	6.0	mΩ
Input Capacitance	C_{iss}	V_{DS} = 10 V		4000		pF
Output Capacitance	C_{oss}	V_{GS} = 0 V		1550		pF
Reverse Transfer Capacitance	C_{rss}	f = 1 MHz		570		pF
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 10 V, I_D = 42 A		23		ns
Rise Time	t_r	V_{GS} = 10 V		23		ns
Turn-off Delay Time	$t_{d(off)}$	R_G = 10 Ω		110		ns
Fall Time	t_f			40		ns
Total Gate Charge	Q_G	V_{DD} = 16 V		68		nC
Gate to Source Charge	Q_{GS}	V_{GS} = 10 V		12		nC
Gate to Drain Charge	Q_{GD}	I_D = 83 A		18		nC
Body Diode Forward Voltage	$V_{F(S-D)}$	I_F = 83 A, V_{GS} = 0 V		1.0		V
Reverse Recovery Time	t_{rr}	I_F = 83 A, V_{GS} = 0 V		77		ns
Reverse Recovery Charge	Q_{rr}	di/dt = 100 A/μs		115		nC

TEST CIRCUIT 1 SWITCHING TIME



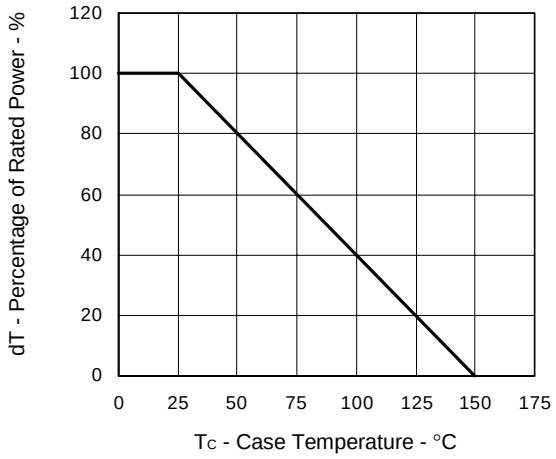
τ = 1 μs
Duty Cycle ≤ 1%

TEST CIRCUIT 2 GATE CHARGE

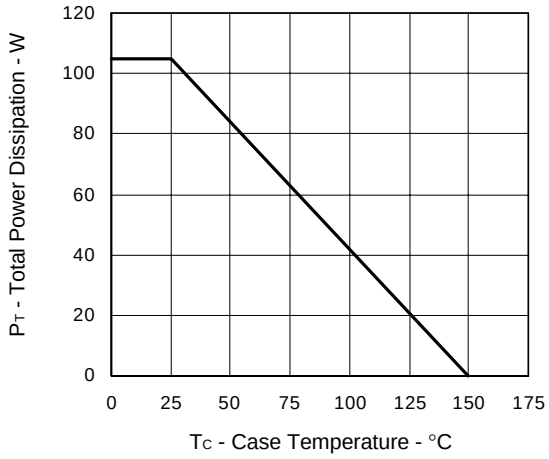


TYPICAL CHARACTERISTICS (T_A = 25°C)

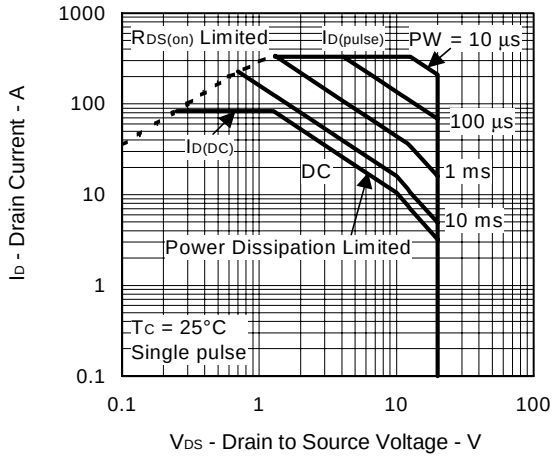
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



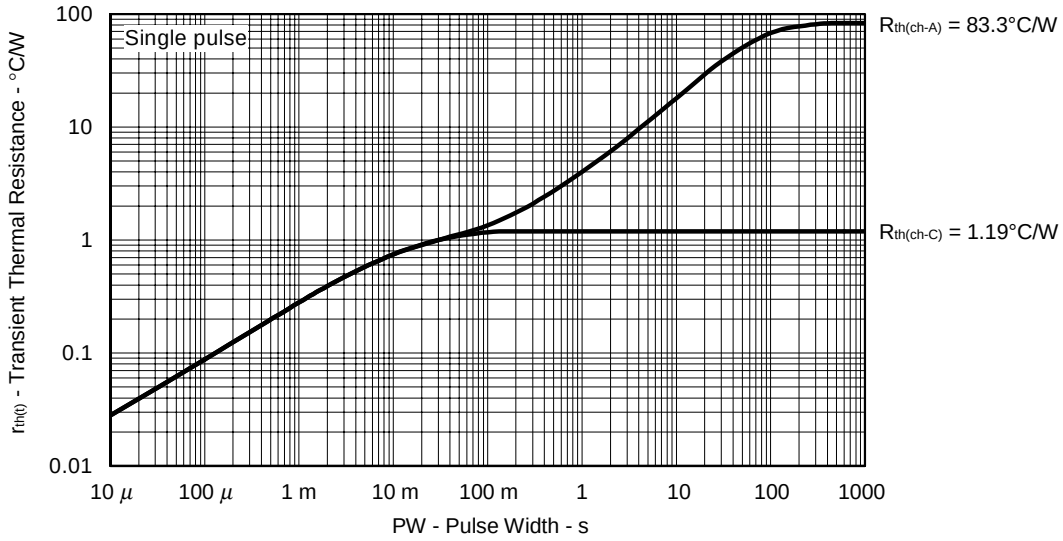
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



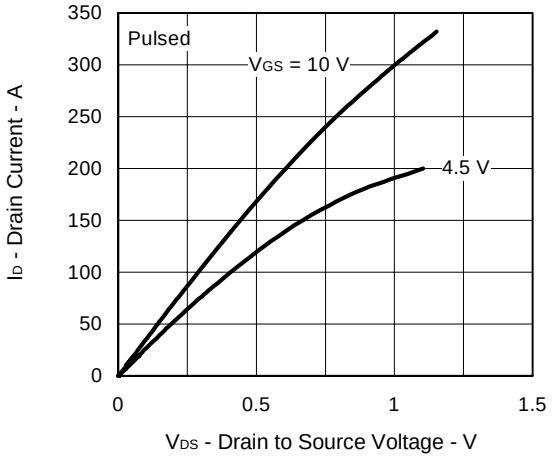
FORWARD BIAS SAFE OPERATING AREA



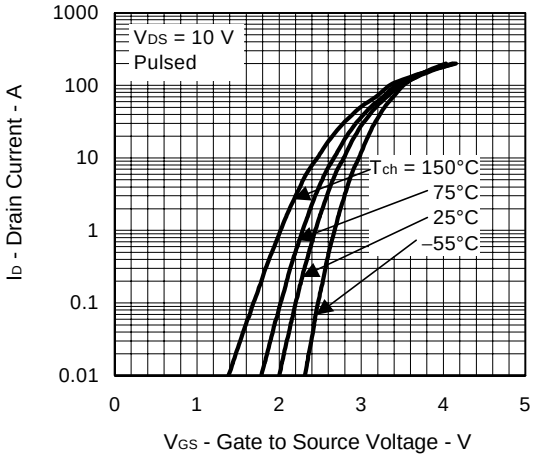
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



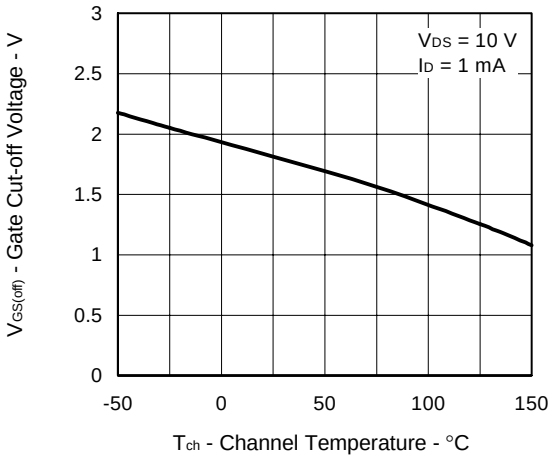
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



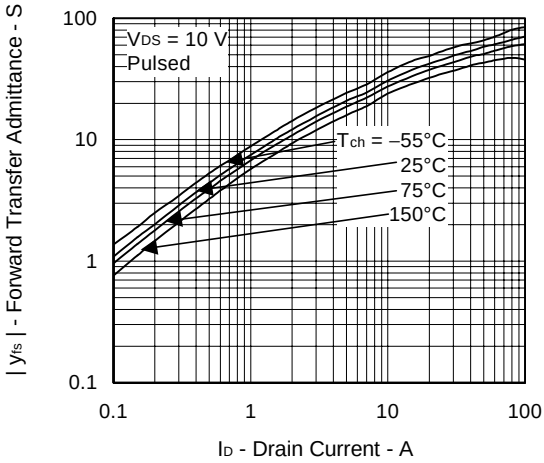
FORWARD TRANSFER CHARACTERISTICS



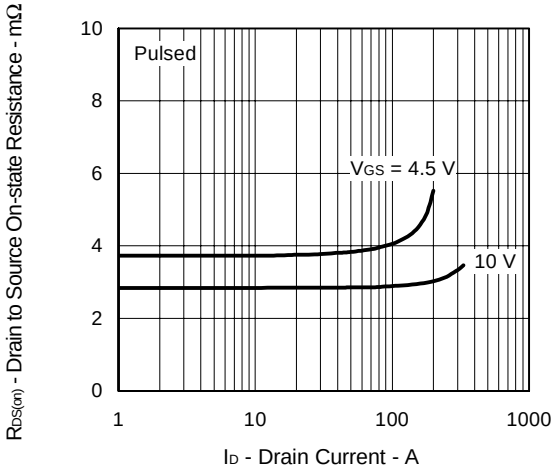
GATE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATURE



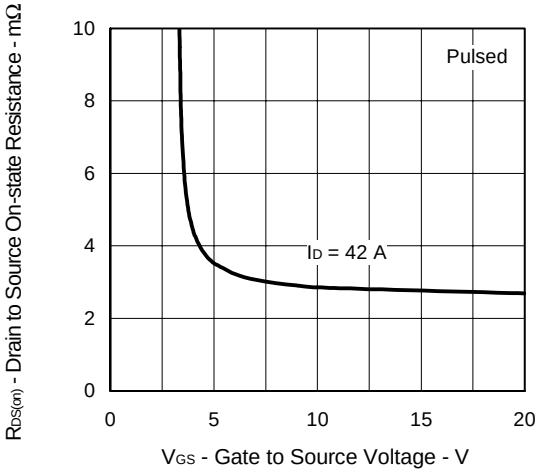
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



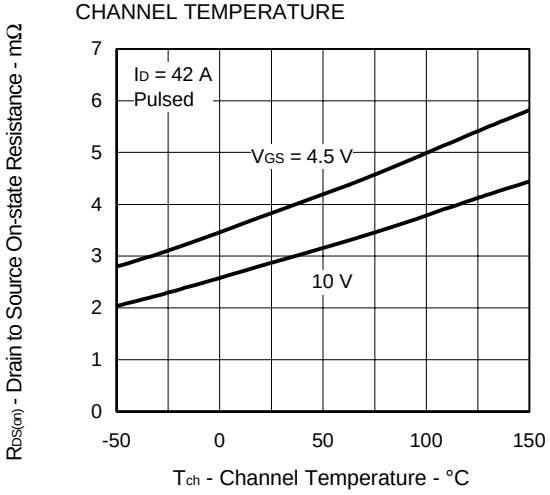
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT



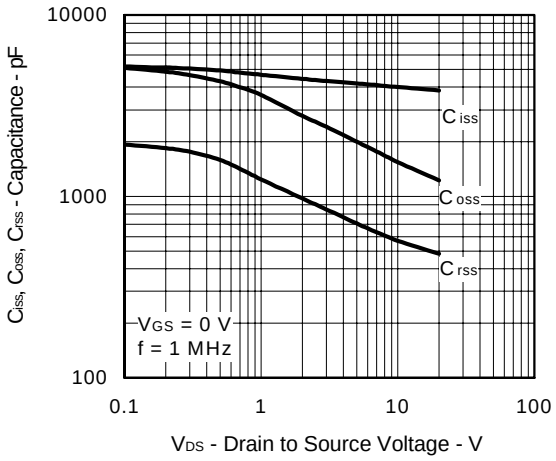
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



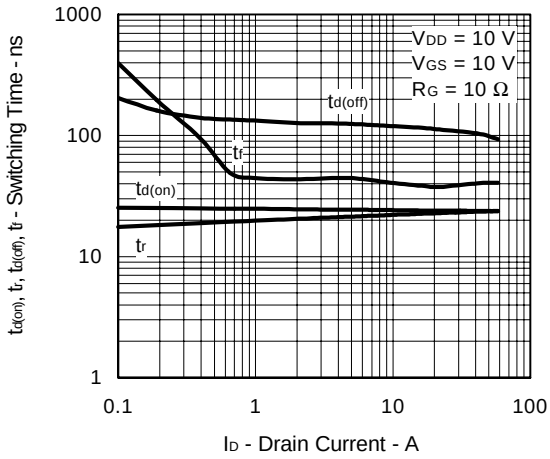
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



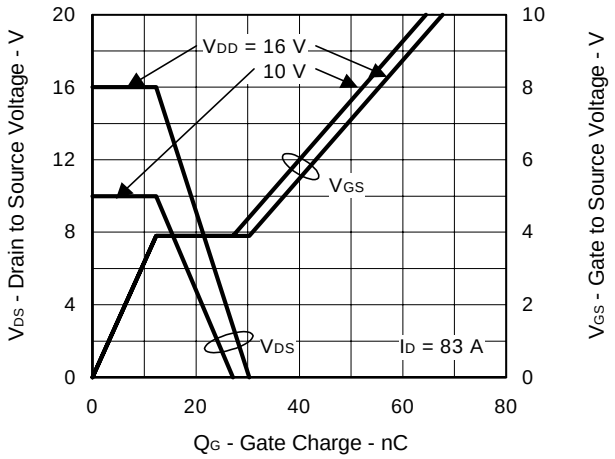
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



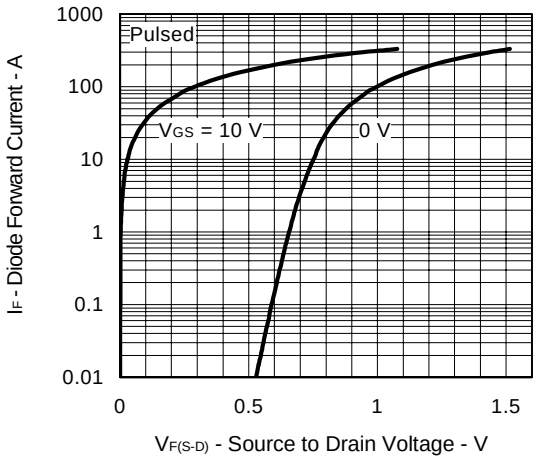
SWITCHING CHARACTERISTICS



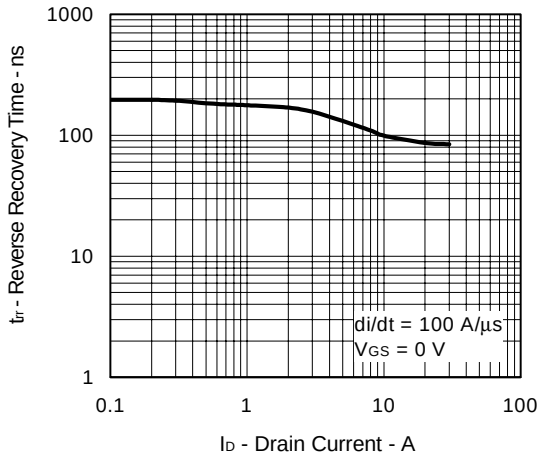
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

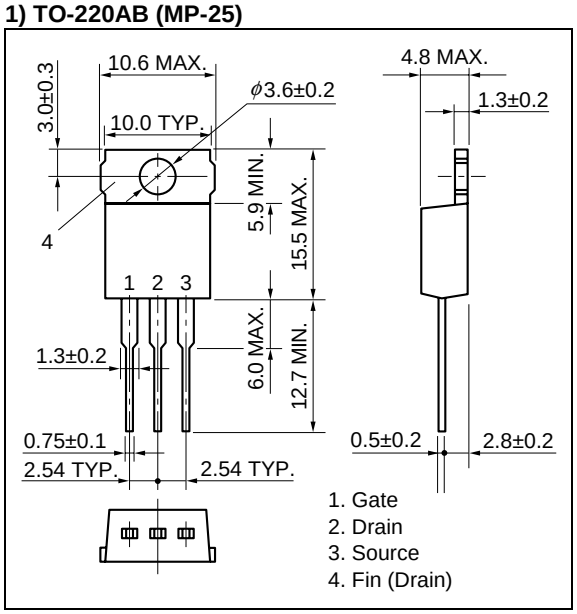


REVERSE RECOVERY TIME vs. DRAIN CURRENT

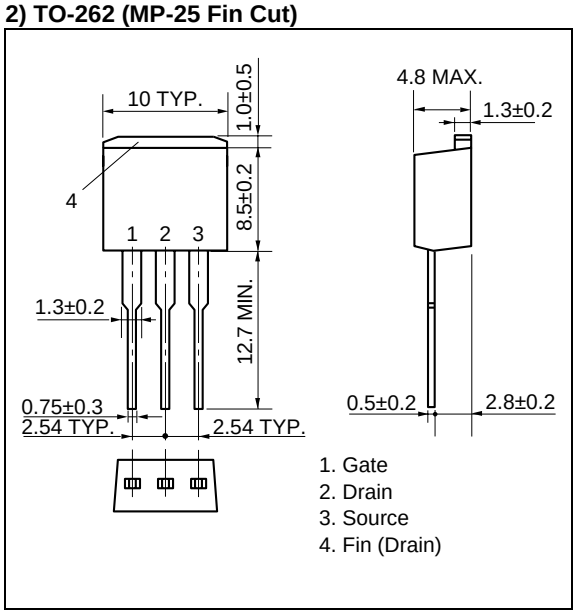


★PACKAGE DRAWINGS (Unit: mm)

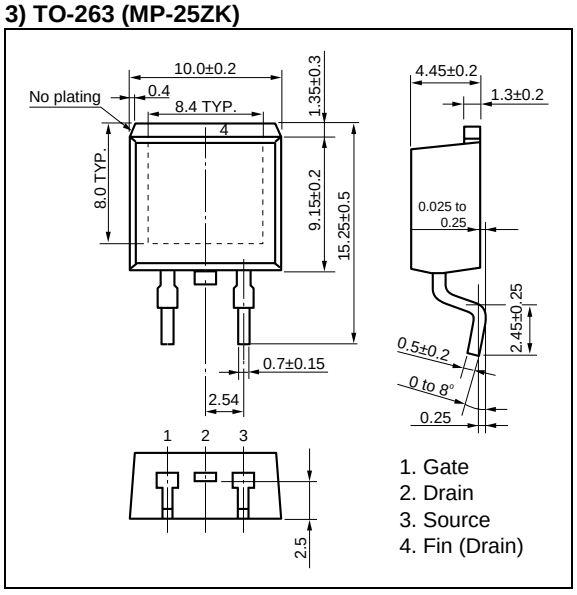
1) TO-220AB (MP-25)



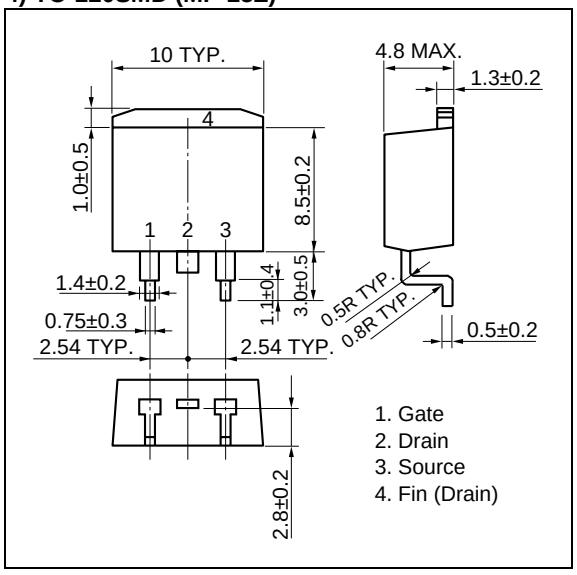
2) TO-262 (MP-25 Fin Cut)



3) TO-263 (MP-25ZK)

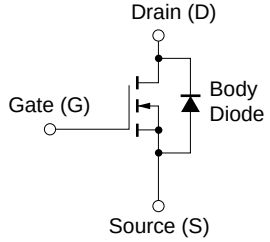


4) TO-220SMD (MP-25Z) Note



Note This package is produced only in Japan.

EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

[MEMO]

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